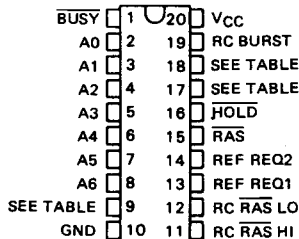


# SN74LS600A, SN74LS601A, SN74LS603A MEMORY REFRESH CONTROLLERS

D2547, JANUARY 1981 — REVISED MARCH 1988

- Controls Refresh Cycle of 4K, 16K, and 64K Dynamic RAMs
- Creates Static RAM Appearance
- Choice of Transparent, Cycle Steal, or Burst Refresh Modes
- 3-State Outputs Drive Bus Lines Directly
- Critical Times Are User RC-Programmable to Optimize System Performance

## SN74LS' . . . DW OR N PACKAGE (TOP VIEW)



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### SELECTION TABLE

DEVICE	REFRESH MODES	MEMORY SIZE	PIN ASSIGNMENTS		
			PIN 9	PIN 17	PIN 18
LS600A	Transparent, Burst	4K or 16K	4K/16K	LATCHED RCO	RESET LATCHED RCO
LS601A	Transparent, Burst	64K	A7	LATCHED RCO	RESET LATCHED RCO
LS603A	Cycle Steal, Burst	64K	A7	READY	RC CYCLE STEAL

### description

The LS600A, LS601A, and LS603A memory refresh controllers contain one 8-bit synchronous counter, nine 3-state buffer drivers, four RC-controlled multivibrators, and other control circuitry on a single monolithic chip. These devices are designed to provide RAS-only refresh on 4K, 16K, and 64K dynamic RAMs. The LS600A and LS601A provide transparent refresh while the LS603A provides cycle-steal refresh. In addition, a burst-mode timer is provided to warn the CPU that the maximum allowable refresh time is about to be violated.

### operating modes

In the transparent refresh mode (LS600A or LS601A), row-refresh cycles occur only during inactive CPU-memory times. In most cases the entire memory refresh sequence can be completed "transparently" without interrupting CPU operations. During idle CPU-memory periods, the REF REQ pins should be taken high so as many rows as possible can be refreshed. A low from BUSY will signal the CPU to wait until the end of that current row refresh before reinstating operations. If all row addresses have been refreshed before the burst-mode timer expires, the burst-mode timer will reset.

If the maximum allowable refresh time of the dynamic RAM is about to be exceeded, the burst mode timer will expire causing the HOLD pin to go low. This signals the CPU that a burst-mode refresh is mandatory and the burst-mode refresh will be accomplished when the CPU takes the REF REQ pins high. To ensure that all rows are refreshed, the address counter is reset to zero whenever the burst-mode timer expires. After the last row has been refreshed, the HOLD pin will return high, and the burst-mode timer will reset. The CPU can then return to normal transparent operation.

A LATCHED RCO output pin is also provided on the LS600A and LS601A to detect when the last row has been refreshed. Upon seeing a RCO from the address counter, the LATCHED RCO output will be set high. This latch is reset by providing a high-going pulse on the RESET LATCHED RCO input.

In the cycle-steal refresh mode (LS603A), refreshing is accomplished by dividing the safe refresh time into equal segments and refreshing one row in each segment. The segment time is programmed via the RC CYCLE STEAL input and will produce a low level on the READY output at the end of each segment period. This indicates to the CPU to suspend operations for one memory cycle for a row refresh. In effect it "steals" one memory cycle from the CPU. After the CPU recognizes the cycle-steal signal from the READY output, it must take both REF REQ pins high. These devices will then refresh one row and return control back to the CPU by taking READY high. The burst-mode timer is also provided to prevent exceeding the maximum allowable refresh time, and operates in the same manner as in the LS600A and LS601A. In applications where the burst-mode timer is not required, it can be disabled by connecting the RC Burst input to ground.

PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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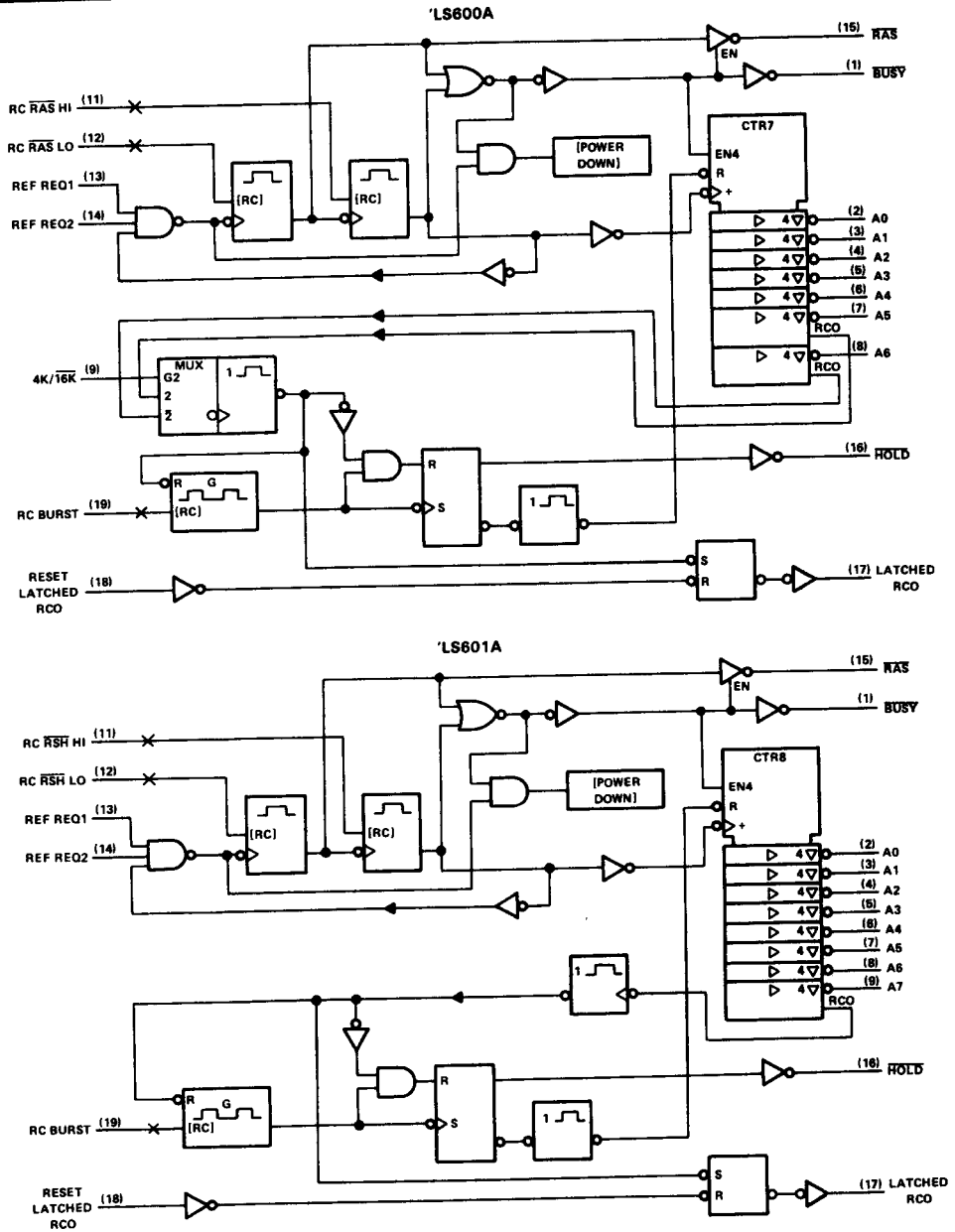
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# SN74LS600A, SN74LS601A MEMORY REFRESH CONTROLLERS

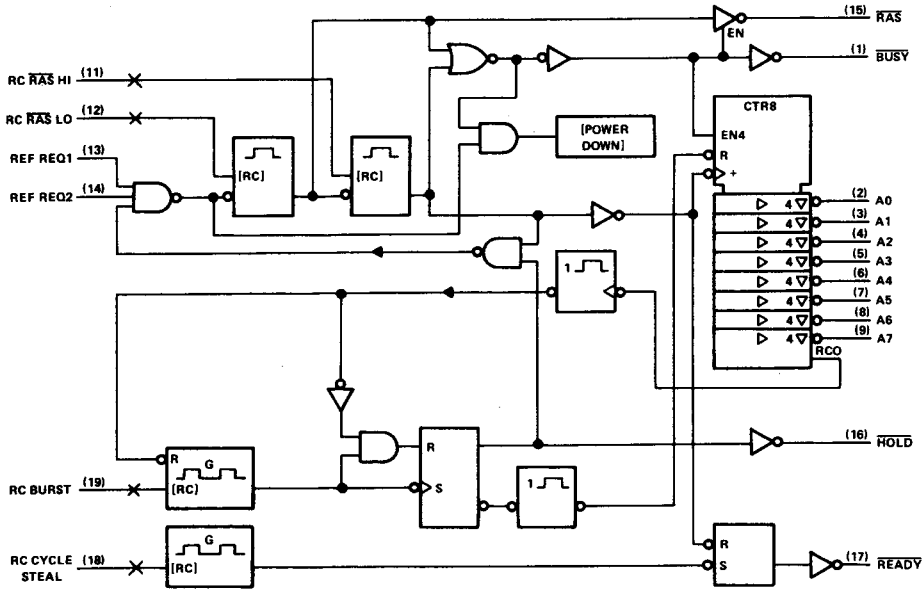
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Pin numbers shown are for DW and N packages.

# SN74LS603A MEMORY REFRESH CONTROLLERS



Pin numbers shown are for DW and N packages.

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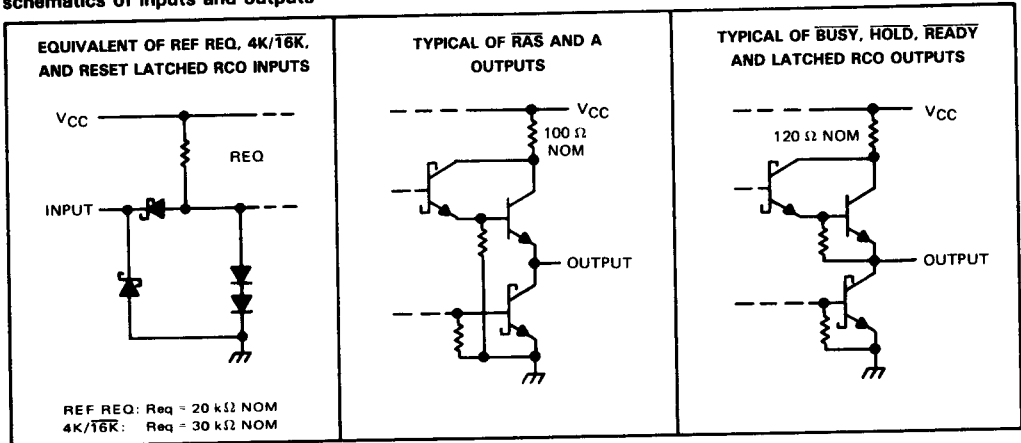
# SN74LS600A, SN74LS601A, SN74LS603A MEMORY REFRESH CONTROLLERS

PIN FUNCTION TABLE

PIN	PIN NAME	FUNCTIONAL DESCRIPTION
1	BUSY	Active output indicates to the CPU that a refresh cycle is in progress.
16	HOLD	Active output should be a priority interrupt to the CPU for emergency burst refresh.
15	RAS	3-state output row address strobe.
11	RC $\overline{\text{RAS}}$ HI	Timing node for high-level portion of RAS. See Note 1.
12	RC RAS LO	Timing node for low-level portion of RAS. See Note 1.
2-8	A0 thru A6	3-state output row address lines.
9	A7	MSB row address line for 'LS601A and 'LS603A (64K-bit memory controllers).
9	4K/ $\overline{\text{T6K}}$	A high input level disables the A5 row address line for 'LS600A. (The high-level input makes the count chain 5 bits long while the low-level makes the count chain 6 bits long.)
17	READY	Interrupt to CPU for cycle steal refresh ('LS603A).
17	LATCHED RCO	Normally high-level, will latch low upon RCO of counter ('LS600A or 'LS601A).
18	RC CYCLE STEAL	Timing node that controls the READY output ('LS600A or 'LS601A). See Note 1.
18	RESET LATCHED RCO	Normally high-level, when pulsed low the LATCHED RCO output will be reset ('LS600A and 'LS601A).
19	RC BURST	Timing node for burst refresh. See Note 1.
13, 14	REF REQ1, REF REQ2	High level on both pins starts and continues row refresh. Low on either pin inhibits refresh.
20, 10	V <sub>CC</sub> , GND	5-V power supply and network ground pins.

NOTE 1: All timing nodes require a resistor to V<sub>CC</sub> and a capacitor to GND.

## schematics of inputs and outputs



## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V <sub>CC</sub> (see Note 2)	7 V
Input voltage	7 V
Off-state output voltage	5.5 V
Operating free-air temperature range	0°C to 70°C
Storage temperature range	-65°C to 150°C

NOTE 2: Voltage values are with respect to network ground terminal.

# SN74LS600A, SN74LS601A, SN74LS603A MEMORY REFRESH CONTROLLERS

## recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, $V_{CC}$		4.75	5	5.25	V
High-level output current, $I_{OH}$	A, $\overline{RAS}$			-2.6	mA
	All others			-400	$\mu$ A
Low-level output current, $I_{OL}$	A, $\overline{RAS}$			24	mA
	All others			8	
Duration or $\overline{RAS}$ output pulse <sup>†</sup>	High, tSHSL		75		ns
	Low, tSLSH		75		
Duration of RESET LATCHED RCO pulse, tRHRL			35		ns
Duration of REF REQ pulse during CYCLE STEAL operation, tQHQL			20		ns
External timing resistor, $R_{ext}$	RC $\overline{RAS}$ LO, RC $\overline{RAS}$ HI		1	6	k $\Omega$
	RC BURST, RC CYCLE STEAL		1	1000	
Operating free-air temperature, $T_A$			0	70	$^{\circ}$ C

<sup>†</sup>Maximum operating frequency for the address counter corresponds to its minimum period, which is the sum of  $t_w(\overline{RAS-H})$  min and  $t_w(\overline{RAS-L})$  min.

## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP <sup>‡</sup>	MAX	UNIT	
$V_{IH}$	High-level input voltage			2			V	
$V_{IL}$	Low-level input voltage					0.8	V	
$V_{IK}$	Input clamp voltage	$V_{CC} = 4.75$ V, $I_I = -1.8$ mA				-1.5	V	
$V_{OH}$	High-level output voltage	A, $\overline{RAS}$	$V_{CC} = 4.75$ V, $V_{IH} = 2$ V, $V_{IL} = 0.8$ V	$I_{OH} = -2.6$ mA	2.4	2.9	V	
		All Others		$I_{OH} = -400$ $\mu$ A	2.7	3.1		
$V_{OL}$	Low-level output voltage	A, $\overline{RAS}$	$V_{CC} = 4.75$ V, $V_{IH} = 2$ V, $V_{IL} = 0.8$ V	$I_{OL} = 12$ mA	0.25 0.4		V	
		All Others		$I_{OL} = 24$ mA	0.35 0.5			
				$I_{OL} = 4$ mA	0.25 0.4			
			$I_{OL} = 8$ mA	0.35 0.5				
$I_{OZH}$	Off-state output current, high-level voltage applied	A, $\overline{RAS}$	$V_{CC} = 5.25$ V REF REQ at $V_{IL} = 0.8$ V	$V_O = 2.7$ V			20	$\mu$ A
$I_{OZL}$	Off-state output current, low-level voltage applied			$V_O = 0.4$ V			-20	$\mu$ A
$I_I$	Input current at maximum input voltage	$V_{CC} = 5.25$ V, $V_I = 7$ V				0.1	mA	
$I_{IH}$	High-level input current	$V_{CC} = 5.25$ V, $V_I = 2.7$ V				20	$\mu$ A	
$I_{IL}$	Low-level input current	$V_{CC} = 5.25$ V, $V_I = 0.4$ V				-0.4	mA	
$I_{OS}$	Short-circuit output current <sup>§</sup>	A, $\overline{RAS}$	$V_{CC} = 5.25$ V			-30	mA	
		All others				-20		
$I_{CC}$	Supply current	$V_{CC} = 5.25$ V, RC $\overline{RAS}$ LO and REF REQ at 0 V		50	85		mA	

<sup>‡</sup>All typical values are at  $V_{CC} = 5$  V,  $T_A = 25^{\circ}$ C.

<sup>§</sup>Not more than one output should be shorted at a time, and duration of the short-circuit should not exceed one second.

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# SN74LS600A, SN74LS601A, SN74LS603A MEMORY REFRESH CONTROLLERS

switching characteristics,  $V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$ , see note 3

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{QHBL}$	REF REQ $\dagger$	BUSY	$C_L = 15\text{ pF}$ , $R_L = 2\text{ k}\Omega$	30	45		ns
$t_{SLBH}^\ddagger$	RAS $\dagger$	BUSY		245	300		ns
$t_{QHSV}$	REF REQ $\dagger$	RAS	$C_L = 320\text{ pF}$ , $R_L = 667\Omega$	47	70		ns
$t_{SHSZ}^\ddagger$	RAS $\dagger$	RAS	$C_L = 5\text{ pF}$ , $R_L = 667\Omega$	245	300		ns
$t_{QHAV}$	REF REQ $\dagger$	ADDRESS	$C_L = 160\text{ pF}$ , $R_L = 667\Omega$	38	65		ns
$t_{SHAZ}^\ddagger$	RAS $\dagger$	ADDRESS	$C_L = 5\text{ pF}$ , $R_L = 667\Omega$	245	300		ns
$t_{RHCL}$	RESET LATCHED	LATCHED	$C_L = 15\text{ pF}$ , $R_L = 2\text{ k}\Omega$	37	55		ns
	RCO $\dagger$	RCO		64	85		ns
$t_{SHYH}$	RAS $\dagger$	READY		210			ns
$t_{SLSH}^\ddagger$	RAS $\dagger$	RAS	$C_L = 320\text{ pF}$ , $R_L = 667\Omega$	245			ns
$t_{SHSL}^\ddagger$	RAS $\dagger$	RAS		3.56			ms
$t_{DHDL}^\ddagger$	HOLD $\dagger$	HOLD	$C_L = 15\text{ pF}$ , $R_L = 2\text{ k}\Omega$	27			$\mu\text{s}$
$t_{YLYL}^\ddagger$	READY $\dagger$	READY					

$^\dagger$  Depends on RC network at pin 11 (4 k $\Omega$ , 200 pF used for testing).

$^\ddagger$  Depends on RC network at pin 12 (4 k $\Omega$ , 200 pF used for testing).

$^\S$  Depends on RC network at pin 19 (680 k $\Omega$ , 0.022  $\mu\text{F}$  used for testing).

$^\P$  Depends on RC network at pin 18 (10 k $\Omega$ , 0.01  $\mu\text{F}$  used for testing).

NOTE 3: Load circuits and voltage waveforms are shown in Section 1.

## explanation of letter symbols

This data sheet uses a new type of letter symbol to describe time intervals. The format is:

$t_{AB-CD}$

where: subscripts A and C indicate the names of the signals for which changes of state or level or establishment of state or level constitute signal events assumed to occur first and last, respectively, that is, at the beginning and end of the time interval.

Subscripts B and D indicate the direction of the transitions and/or the final states or levels of the signals represented by A and C, respectively. One or two of the following is used:

- H = high or transition to high
- L = low or transition to low
- V = a valid steady-state level
- X = unknown, changing, or "don't care" level
- Z = high-impedance (off) state.

The hyphen between the B and C subscripts is omitted when no confusion is likely to occur. For these letter symbols on this data sheet, the signal names are further abbreviated as follows:

SIGNAL NAME	A or C SUBSCRIPT
BUSY	B
HOLD	D
RAS	S
A0 - A7	A
READY	Y
LATCHED RCO	C
RESET LATCHED RCO	R
REF REQ	Q

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TIMING DIAGRAMS

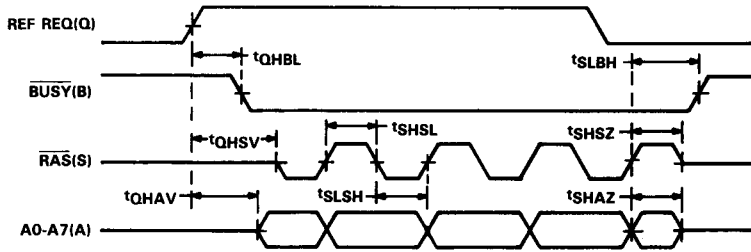


FIGURE 1 - TRANSPARENT REFRESH

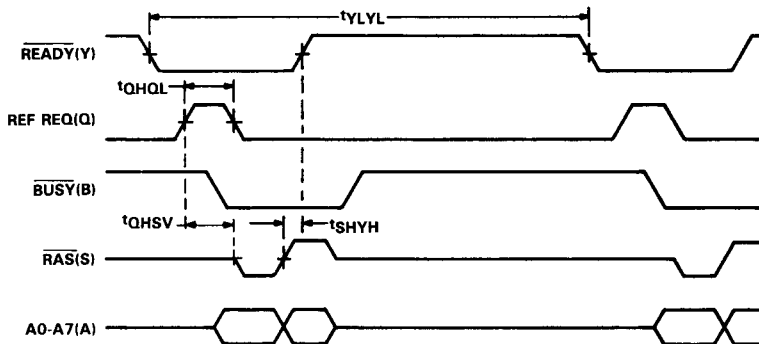
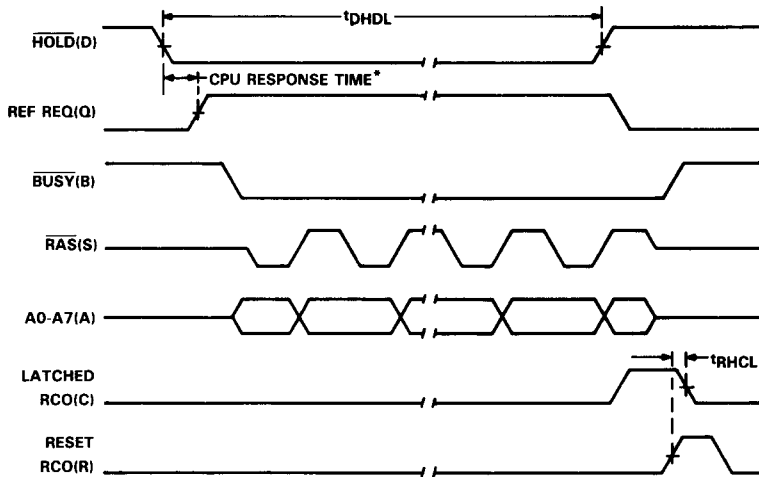


FIGURE 2 - CYCLE STEAL REFRESH



\* During testing, an 'LS04 is used to invert  $\overline{\text{HOLD}}$  to provide the REF REQ input.

FIGURE 3 - BURST MODE REFRESH

**SN74LS600A, SN74LS601A, SN74LS603A  
MEMORY REFRESH CONTROLLERS**

**TYPICAL CHARACTERISTICS**

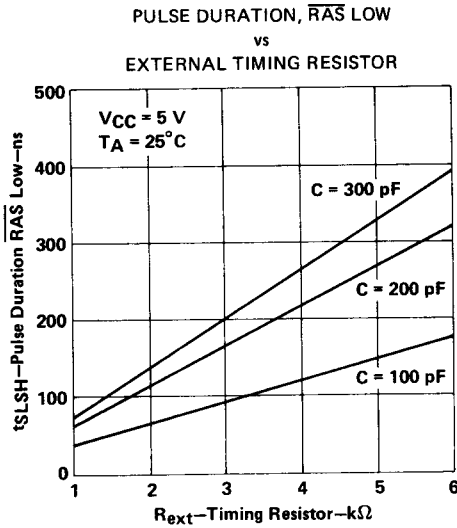


FIGURE 4

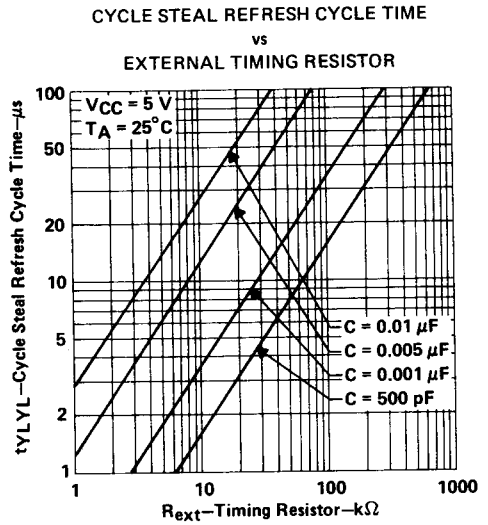


FIGURE 5

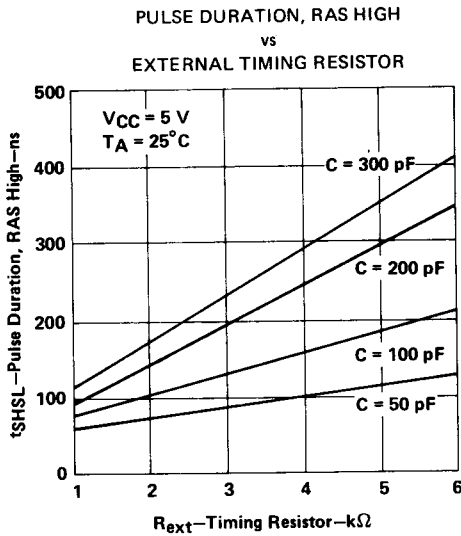


FIGURE 6

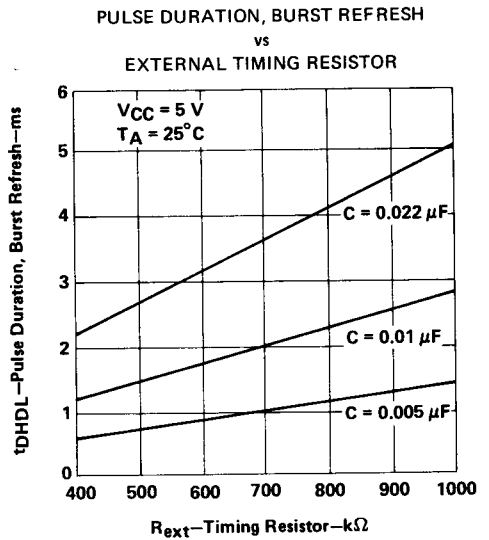


FIGURE 7

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